

NTB5860N, NTP5860N, NVB5860N

N-Channel Power MOSFET

60 V, 220 A, 3.0 mΩ

Features

- Low $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant
- NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ Unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	60	V
Gate-to-Source Voltage – Continuous			V_{GS}	± 20	V
Continuous Drain Current, $R_{\theta JC}$	Steady State	$T_C = 25^{\circ}\text{C}$	I_D	220	A
		$T_C = 100^{\circ}\text{C}$		156	
Power Dissipation, $R_{\theta JC}$	Steady State	$T_C = 25^{\circ}\text{C}$	P_D	283	W
Pulsed Drain Current	$t_p = 10\ \mu\text{s}$		I_{DM}	660	A
Current Limited by Package			I_{DMmax}	130	A
Operating and Storage Temperature Range			T_J, T_{stg}	-55 to +175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	130	A
Single Pulse Drain-to-Source Avalanche Energy ($L = 0.3\ \text{mH}$)			E_{AS}	735	mJ
Lead Temperature for Soldering Purposes (1/8" from Case for 10 Seconds)			T_L	260	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) Steady State	$R_{\theta JC}$	0.53	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	28	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

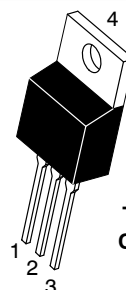
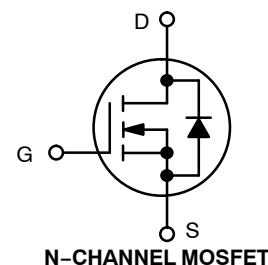
1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).



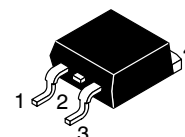
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
60 V	3.0 mΩ @ 10 V	220 A

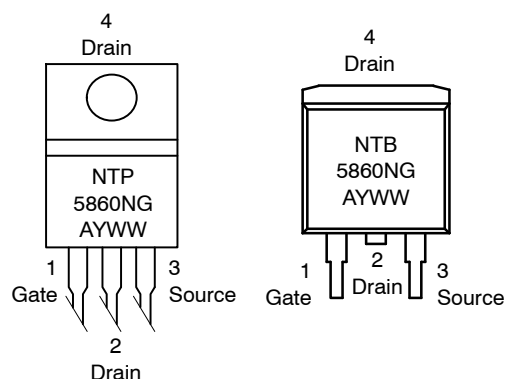


TO-220AB
CASE 221A
STYLE 5



D²PAK
CASE 418B
STYLE 2

MARKING DIAGRAMS & PIN ASSIGNMENTS



G = Pb-Free Device
A = Assembly Location*
Y = Year
WW = Work Week

*Could be one or two digit alpha or numeric code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTB5860N, NTP5860N, NVB5860N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ Unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		5.0		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$ $V_{DS} = 60\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
Threshold Temperature Coefficient	$V_{GS(th)}/T_J$			-10.1		mV/ $^\circ\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 75\text{ A}$		2.5	3.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		38		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		10760		pF
Output Capacitance	C_{oss}			1125		
Transfer Capacitance	C_{rss}			700		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 48\text{ V},$ $I_D = 65\text{ A}$		180		nC
Threshold Gate Charge	$Q_{G(TH)}$			11		
Gate-to-Source Charge	Q_{GS}			45		
Gate-to-Drain Charge	Q_{GD}			57		

SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{ V}$ (Note 3)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DD} = 48\text{ V},$ $I_D = 65\text{ A}, R_G = 2.5\text{ }\Omega$		27		ns
Rise Time	t_r			117		
Turn-Off Delay Time	$t_{d(off)}$			66		
Fall Time	t_f			150		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}$ $I_S = 20\text{ A}$	$T_J = 25^\circ\text{C}$		0.76	1.1	V_{dc}
			$T_J = 125^\circ\text{C}$		0.63		
Reverse Recovery Time	t_{rr}	$V_{GS} = 0\text{ V}, I_S = 65\text{ A},$ $di_S/dt = 100\text{ A}/\mu\text{s}$			55		ns
Charge Time	t_a				29		
Discharge Time	t_b				26		
Reverse Recovery Stored Charge	Q_{RR}				76		nC

- Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

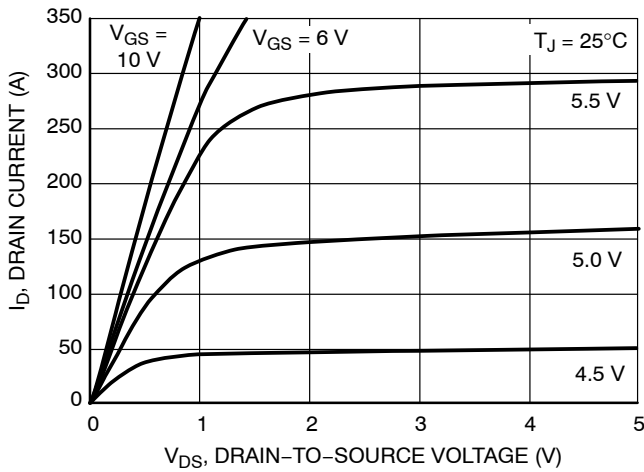


Figure 1. On-Region Characteristics

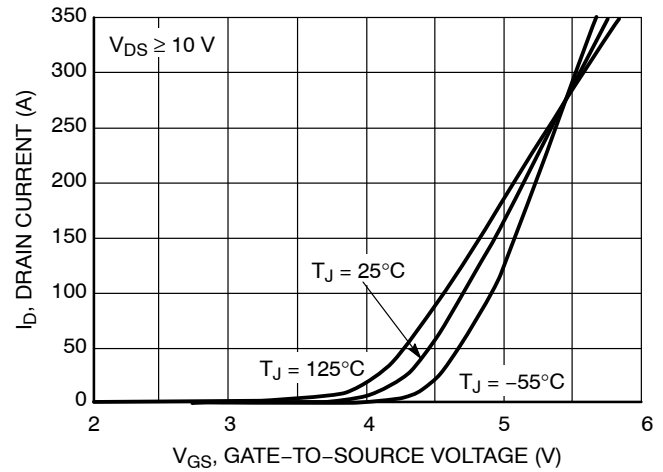


Figure 2. Transfer Characteristics

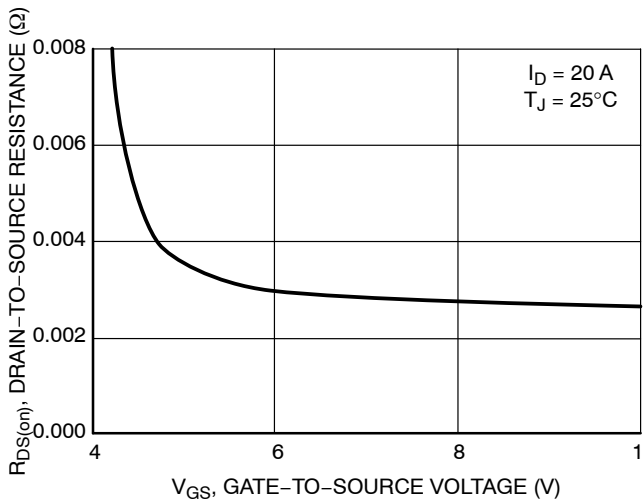


Figure 3. On-Resistance vs. Gate Voltage

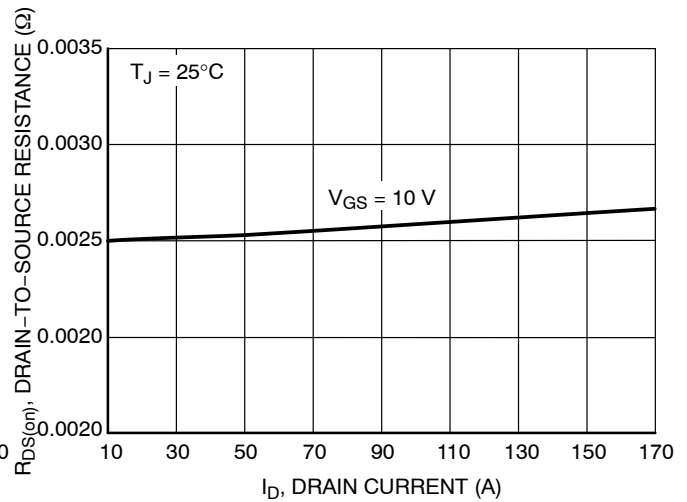


Figure 4. On-Resistance vs. Drain Current

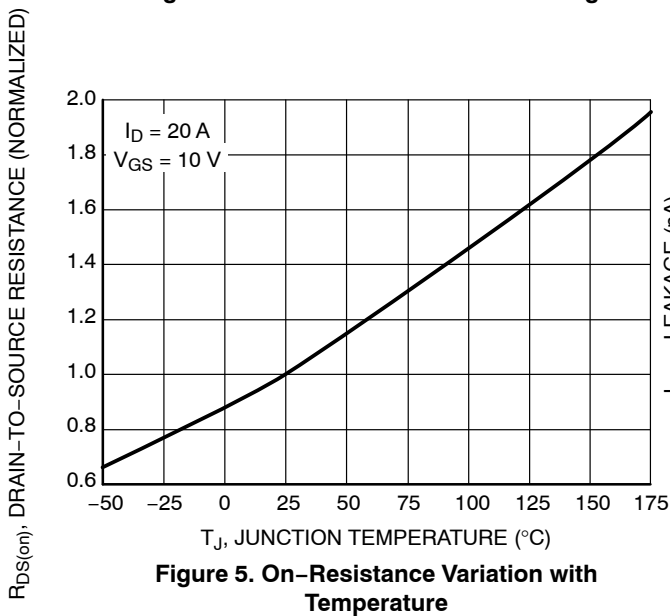


Figure 5. On-Resistance Variation with Temperature

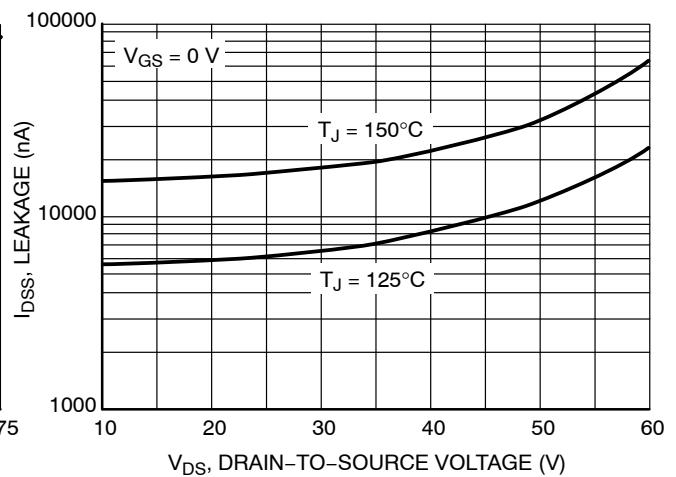


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

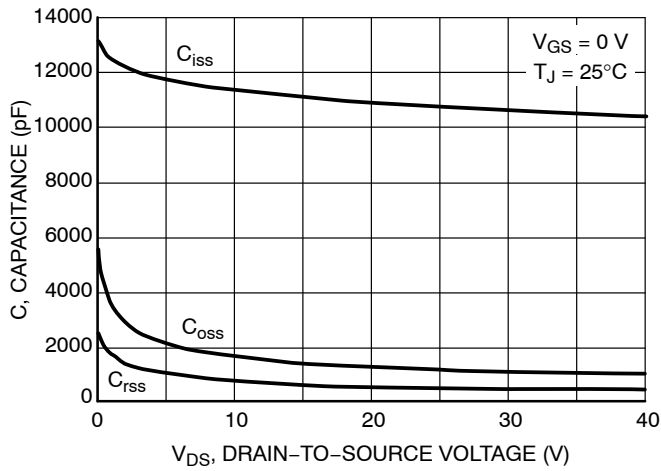


Figure 7. Capacitance Variation

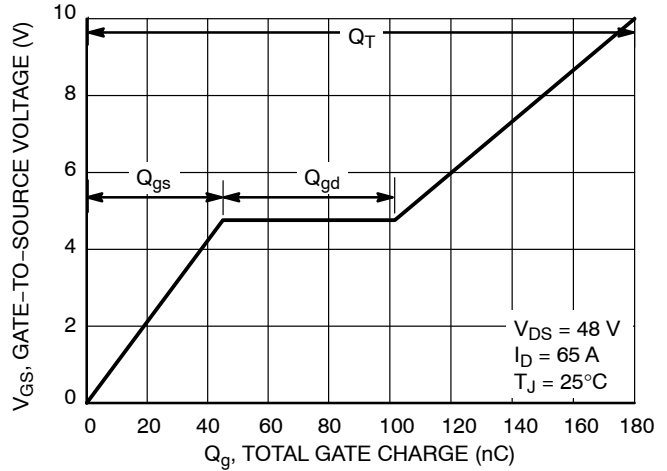


Figure 8. Gate-to-Source vs. Total Charge

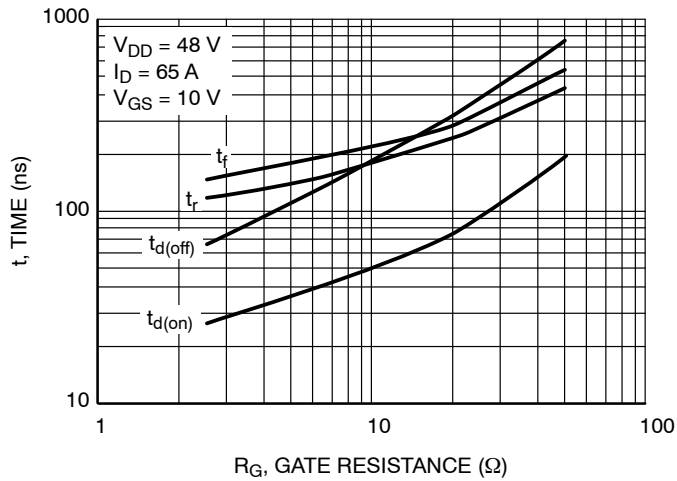


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

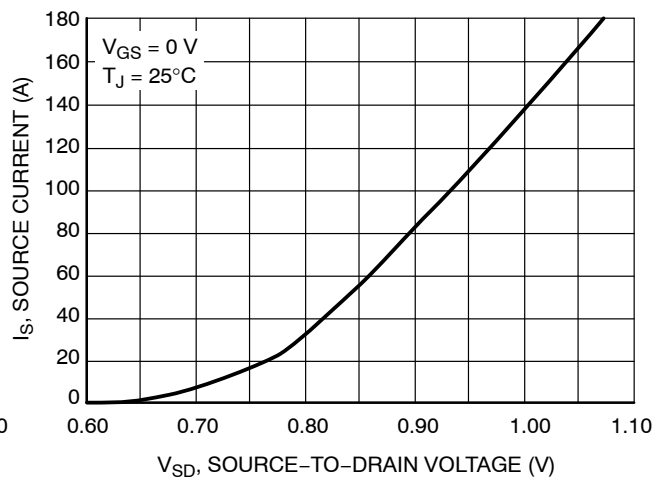


Figure 10. Diode Forward Voltage vs. Current

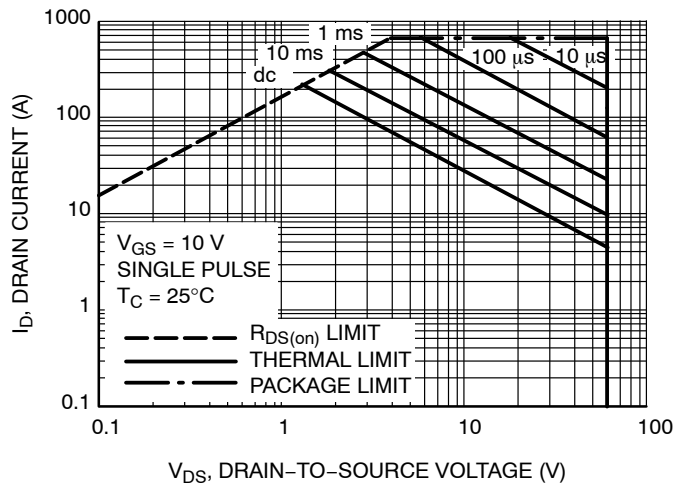


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTB5860N, NTP5860N, NVB5860N

TYPICAL CHARACTERISTICS

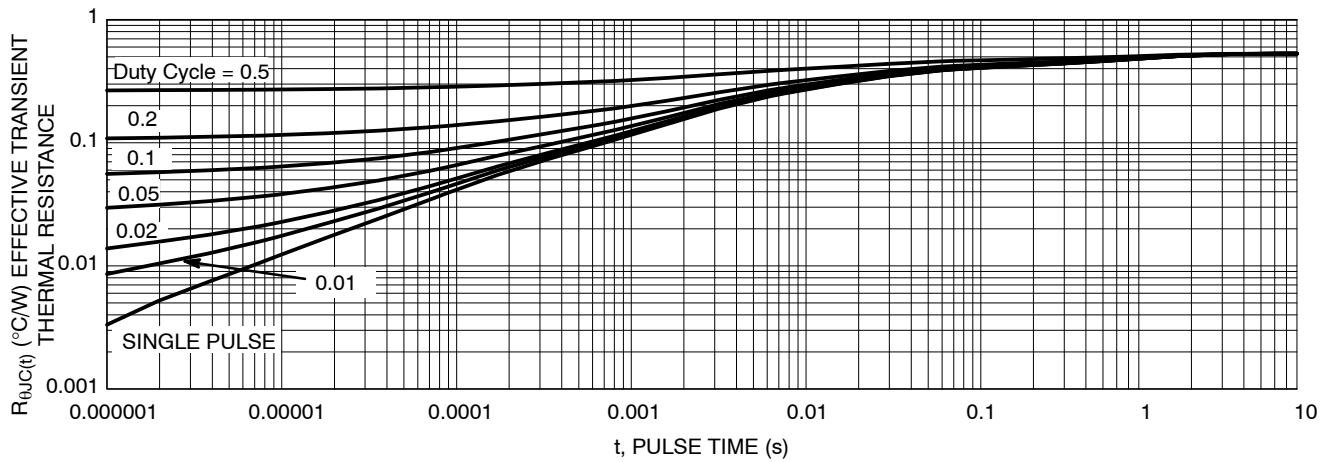


Figure 12. Thermal Response

ORDERING INFORMATION

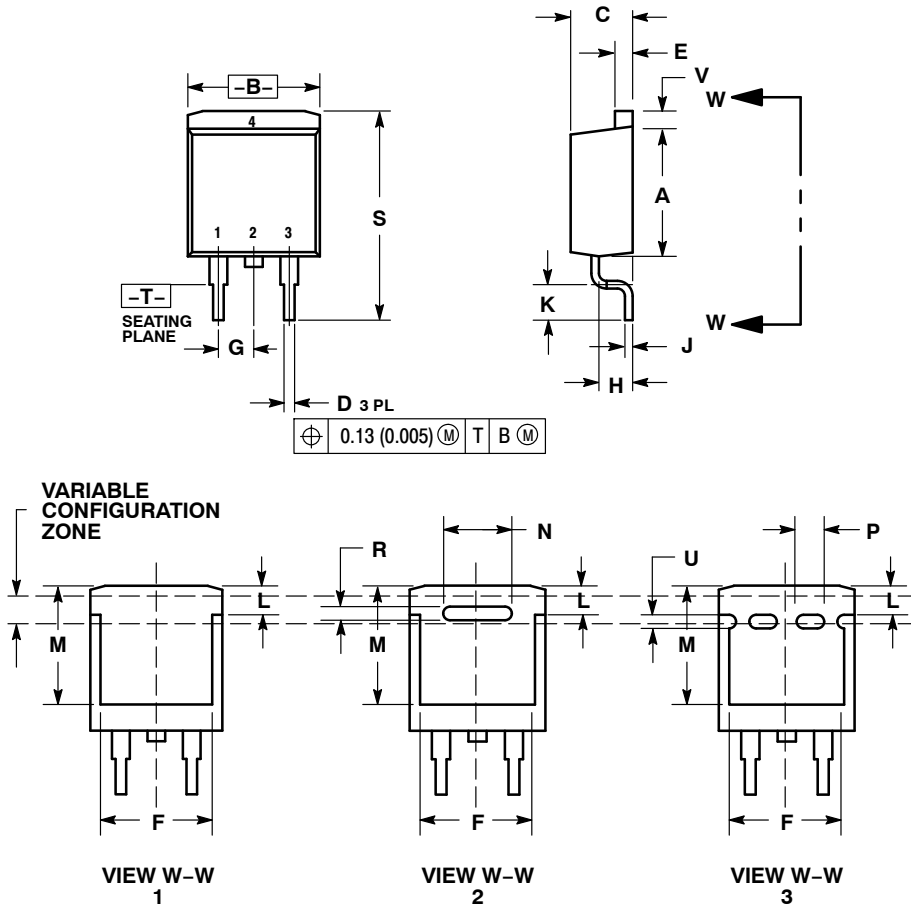
Device	Package	Shipping [†]
NTP5860NG	TO-220AB (Pb-Free)	50 Units / Rail
NTB5860NT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NVB5860NT4G*	D ² PAK (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

D²PAK
CASE 418B-04
ISSUE J

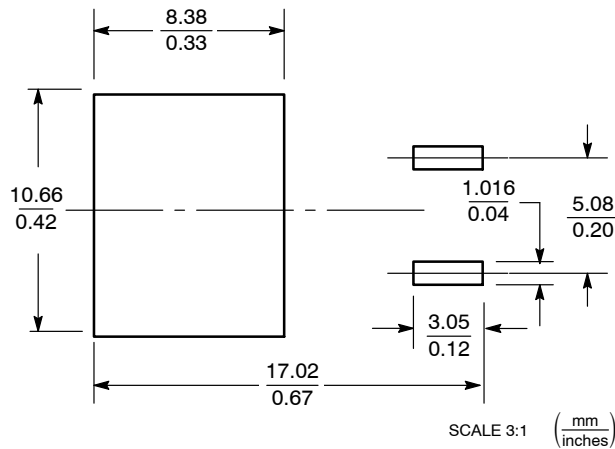


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

- STYLE 2:
1. GATE
 2. DRAIN
 3. SOURCE
 4. DRAIN

SOLDERING FOOTPRINT*

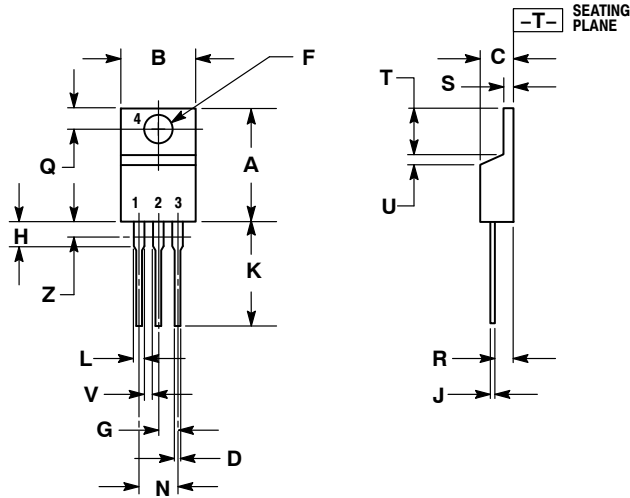


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTB5860N, NTP5860N, NVB5860N

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AF



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 5:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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NTB5860N/D



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Наши преимущества:

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- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
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- Экспресс доставка в любую точку России;
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Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.